



### Product Summary

V <sub>(BR)DSS</sub>	R <sub>DS(on)TYP</sub>	I <sub>D</sub>
30V	35mΩ@10V	4A
	39mΩ@4.5V	
	50mΩ@2.5V	

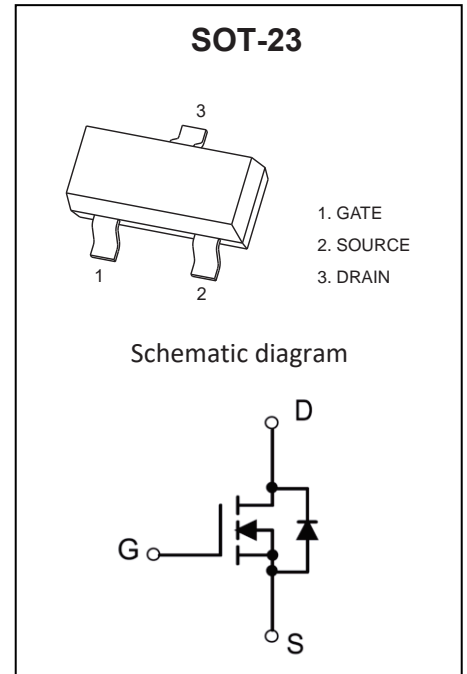
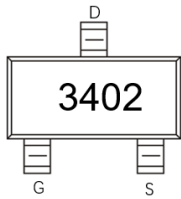
### Feature

- Trench Technology Power MOSFET
- Low R<sub>DS(ON)</sub>
- Low Gate Charge

### Application

- Load Switch
- DC/DC Converter

### MARKING:



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V <sub>DS</sub>	30	V
Gate - Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current <sup>1,5</sup>	I <sub>D</sub>	4	A
	T <sub>A</sub> = 25°C		
Pulsed Drain Current <sup>2</sup>	I <sub>DM</sub>	12	A
Power Dissipation <sup>4,5</sup>	P <sub>D</sub>	0.35	W
	T <sub>A</sub> = 25°C		
Thermal Resistance from Junction to Ambient <sup>5</sup>	R <sub>θJA</sub>	357	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C

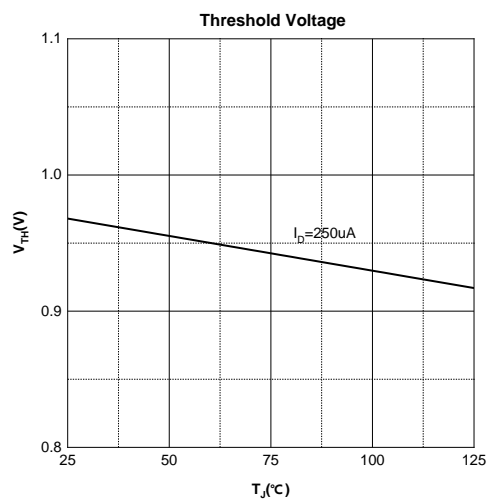
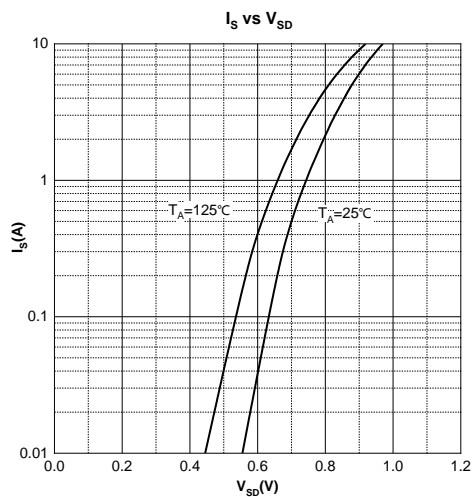
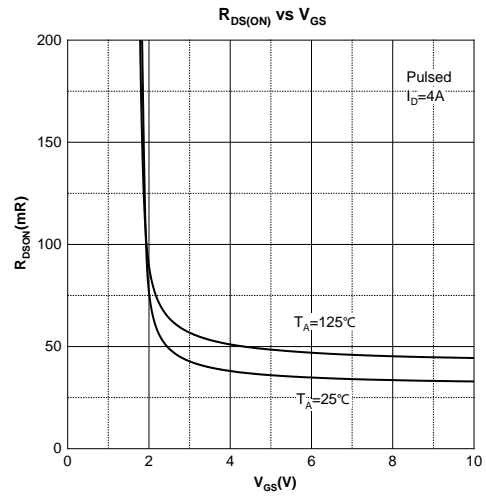
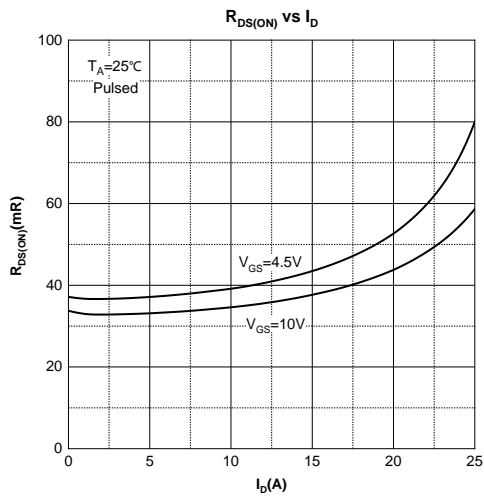
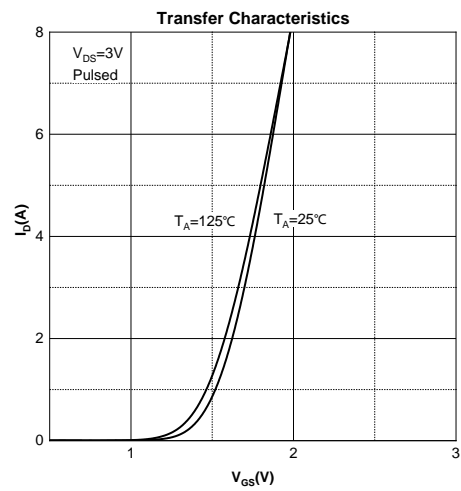
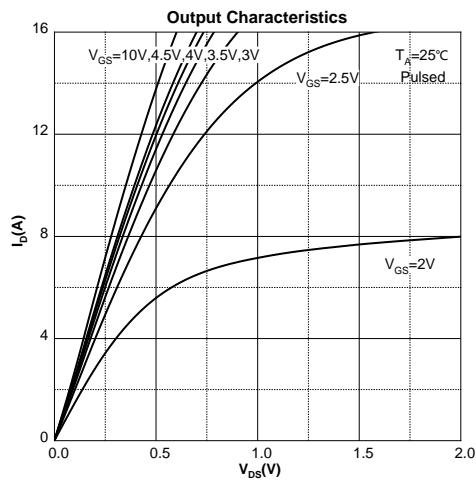
## MOSFET ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>3</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	1.0	1.5	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4A$		35	52	m $\Omega$
		$V_{GS} = 4.5V, I_D = 3A$		39	65	
		$V_{GS} = 2.5V, I_D = 2A$		50	85	
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$		369		pF
Output Capacitance	$C_{oss}$			39		
Reverse Transfer Capacitance	$C_{rss}$			34		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.0		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 15V, V_{GS} = 10V, I_D = 4A$		9.9		nC
Gate-source Charge	$Q_{gs}$			0.7		
Gate-drain Charge	$Q_{gd}$			1.8		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 15V, V_{GS} = 10V, R_L = 3.75\Omega, R_G = 6\Omega$		3.5		ns
Turn-on Rise Time	$t_r$			1.2		
Turn-off Delay Time	$t_{d(off)}$			55		
Turn-off Fall Time	$t_f$			2.2		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 2A$			1.2	V

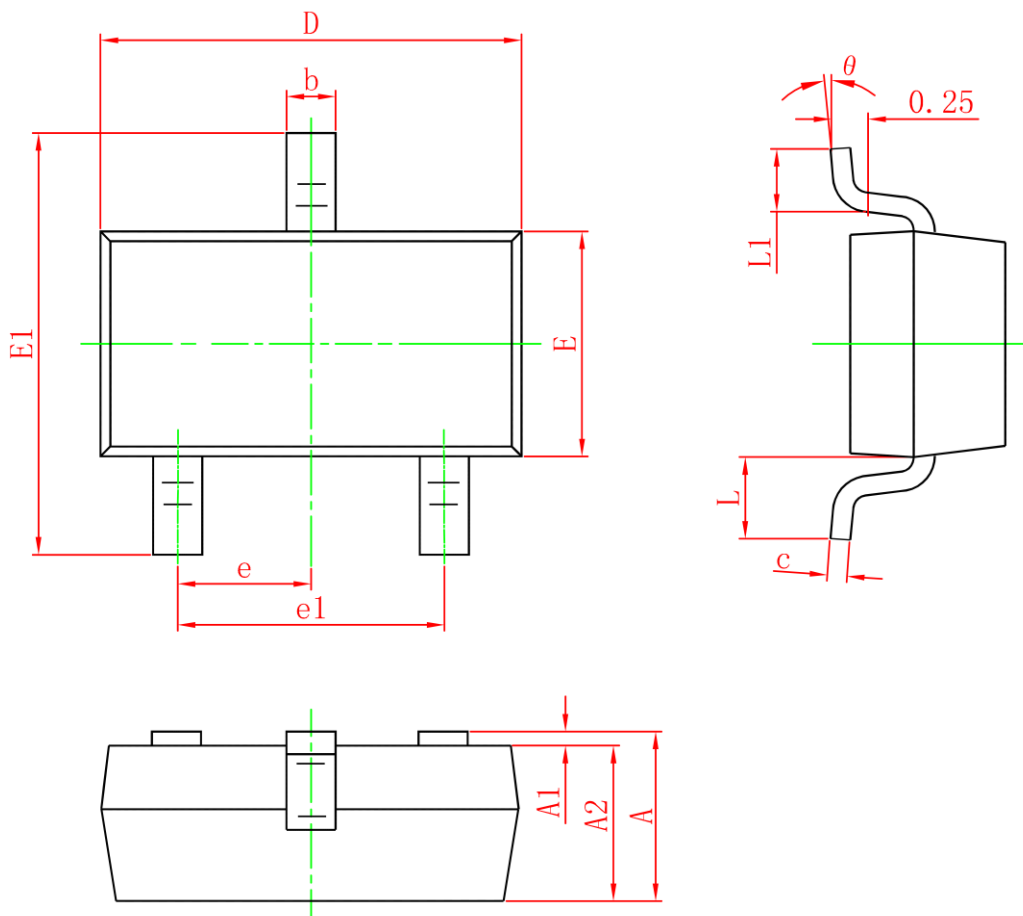
Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 4.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ .
- 5.Device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

**Typical Characteristics**



## SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0	0.100	0	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.150	1.500	0.045	0.059
E1	2.250	2.650	0.089	0.104
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°